Jaehyuk Park

List of Publications by Year
in descending order

19	501	759233 12	996975 15
papers	citations	h-index	g-index

19	19	19	605
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Various Threshold Switching Devices for Integrate and Fire Neuron Applications. Advanced Electronic Materials, 2019, 5, 1800866.	5.1	91
2	Comprehensive scaling study of NbO2 insulator-metal-transition selector for cross point array application. Applied Physics Letters, 2016, 108, .	3.3	84
3	Multi-layered NiOy/NbOx/NiOy fast drift-free threshold switch with high Ion/Ioff ratio for selector application. Scientific Reports, 2017, 7, 4068.	3.3	59
4	Field-induced nucleation in threshold switching characteristics of electrochemical metallization devices. Applied Physics Letters, 2017, 111, .	3.3	54
5	Dynamics of electroforming and electrically driven insulator-metal transition in NbOx selector. Applied Physics Letters, 2016, 108, .	3.3	42
6	3D Stackable and Scalable Binary Ovonic Threshold Switch Devices with Excellent Thermal Stability and Low Leakage Current for Highâ€Density Crossâ€Point Memory Applications. Advanced Electronic Materials, 2019, 5, 1900196.	5.1	27
7	Retention modeling for ultra-thin density of Cu-based conductive bridge random access memory (CBRAM). AIP Advances, 2016, 6, .	1.3	25
8	Steep Slope Field-Effect Transistors With Bâ€“Te-Based Ovonic Threshold Switch Device. IEEE Journal of the Electron Devices Society, 2018, 6, 821-824.	2.1	22
9	Improved threshold switching characteristics of multi-layer NbOx for 3-D selector application. Microelectronic Engineering, 2015, 147, 318-320.	2.4	21
10	NbO₂-Based Frequency Storable Coupled Oscillators for Associative Memory Application. IEEE Journal of the Electron Devices Society, 2018, 6, 250-253.	2.1	19
11	Understanding of the Abrupt Resistive Transition in Different Types of Threshold Switching Devices From Materials Perspective. IEEE Transactions on Electron Devices, 2020, 67, 2878-2883.	3.0	14
12	Hybrid Selector With Excellent Selectivity and Fast Switching Speed for X-Point Memory Array. IEEE Electron Device Letters, 2018, 39, 1171-1174.	3.9	13
13	Field-induced nucleation switching in binary ovonic threshold switches. Applied Physics Letters, 2019, 115, .	3.3	10
14	CMOS compatible low-power volatile atomic switch for steep-slope FET devices. Applied Physics Letters, 2018, 113, .	3.3	7
15	Communicationâ€”Reduced Off-Current of NbO₂by Thermal Oxidation of Polycrystalline Nb Wire. ECS Journal of Solid State Science and Technology, 2017, 6, P641-P643.	1.8	5
16	Selector devices for emerging memories. , 2020, , 135-164.		5
17	Selector devices for x-point memory. , 2019, , 365-390.		2
18	Effect of TiO<inf>x</inf>-based tunnel barrier on non-linearity and switching reliability of resistive random access memory. , 2014, , .		1

#	Article	IF	Citations
19	Effect of nitrogen-doped GST buffer layer on switching characteristics of conductive-bridging RAM. , 2014, , .		0